

Reflections on the first year of PLD of HTS thin films  
& recent advances in PLD of  
Topological superconducting NbN-Bi<sub>2</sub>Se<sub>3</sub>-Au junctions



Gad Koren

*Physics Department, Technion – Israel Institute of Technology  
Haifa, 32000, ISRAEL*

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# Reminiscences from the first year of PLD of HTS thin films 1987-1988

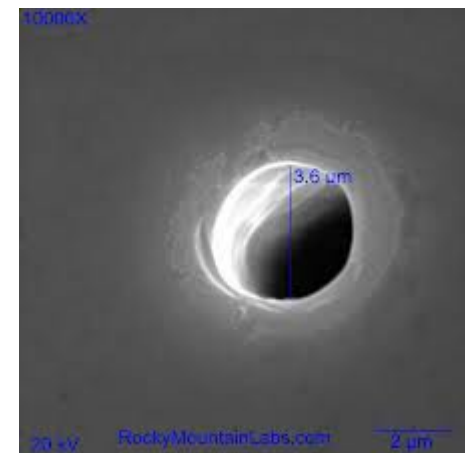
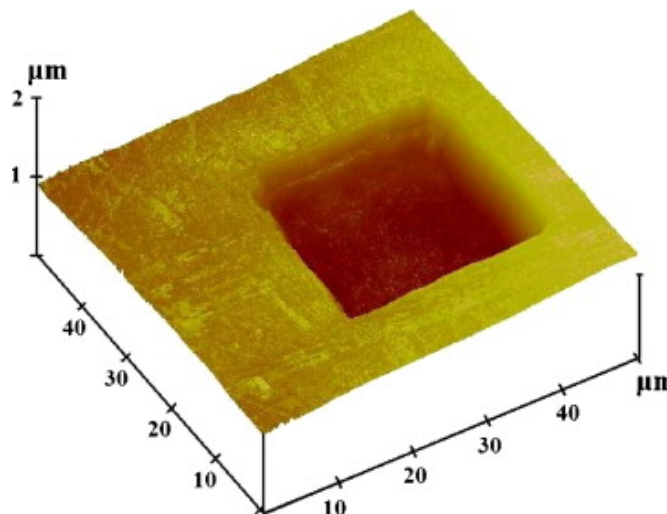
Preparation of the high temperature superconducting (HTS) thin films by pulsed laser deposition (PLD)

- 1-2-3 YBCO target
- pinkish plume



- Prior to 1987, I was working in UV laser ablation for etching of polymers & solids

The plume looks similar to the above, but the end result is a via-hole in the target





## Moving from etching to deposition (1987-8)

- Since the UV laser ablation process was familiar to me, I moved quickly to deposition of HTS thin films by PLD
- It was easy to prepare ceramics film by PLD at low temperature and a post annealing process
- First, we wished to have *in-situ* annealing – necessitates 700-800 °C heater blocks (the stoichiometry of the 1-2-3 YBCO was preserved, since it is a stable phase) [even 2-1-1 yields 1-2-3 in PLD...]
- The second challenge was not to lose, or to stabilize, the YBCO phase during the deposition process – Oxygen role - below ~5-10 mTorr O<sub>2</sub> pressure, the 1-2-3 YBCO loses its stoichiometry due to Cu<sub>2</sub>O evaporation – very volatile
- Venky's paper: APL **52**, 754 (1988) – used 5 mTorr & post annealing
- Our paper: APL **53**, 2330 (1988) – used 100 mTorr & *in-situ* anneal.
- Epitaxiality - lattice mismatch – SrTiO<sub>3</sub>, LaGaO<sub>3</sub>, NdGaO<sub>3</sub>, LaAlO<sub>3</sub>.....  
Work done in IBM Research, Yorktown, NY, 1989 →

## My sabbatical in the IBM Research lab, Yorktown Heights, NY, 1988-9



- I brought the PLD technique, that was developed at the Technion, to the IBM Research lab (I was working in the group of Arunava Gupta)
- Work on epitaxiality and smoothness of the films versus the laser-wavelength, was done there.
- One day we had a visitor from Bellcore, Venky Venkatesan. He told us he was very relieved to see our APL paper on PLD from 1988, since this removed doubts in his own work, as people complained to him that they could not reproduce his results... (I guess this was due to the 5 mTorr deposition in that paper)
- So far for nostalgia,  
and now we shall move to research of these days

# Proximity induced triplet superconductivity in doped topological $\text{Bi}_2\text{Se}_3$ films in contact with the s-wave superconductor NbN

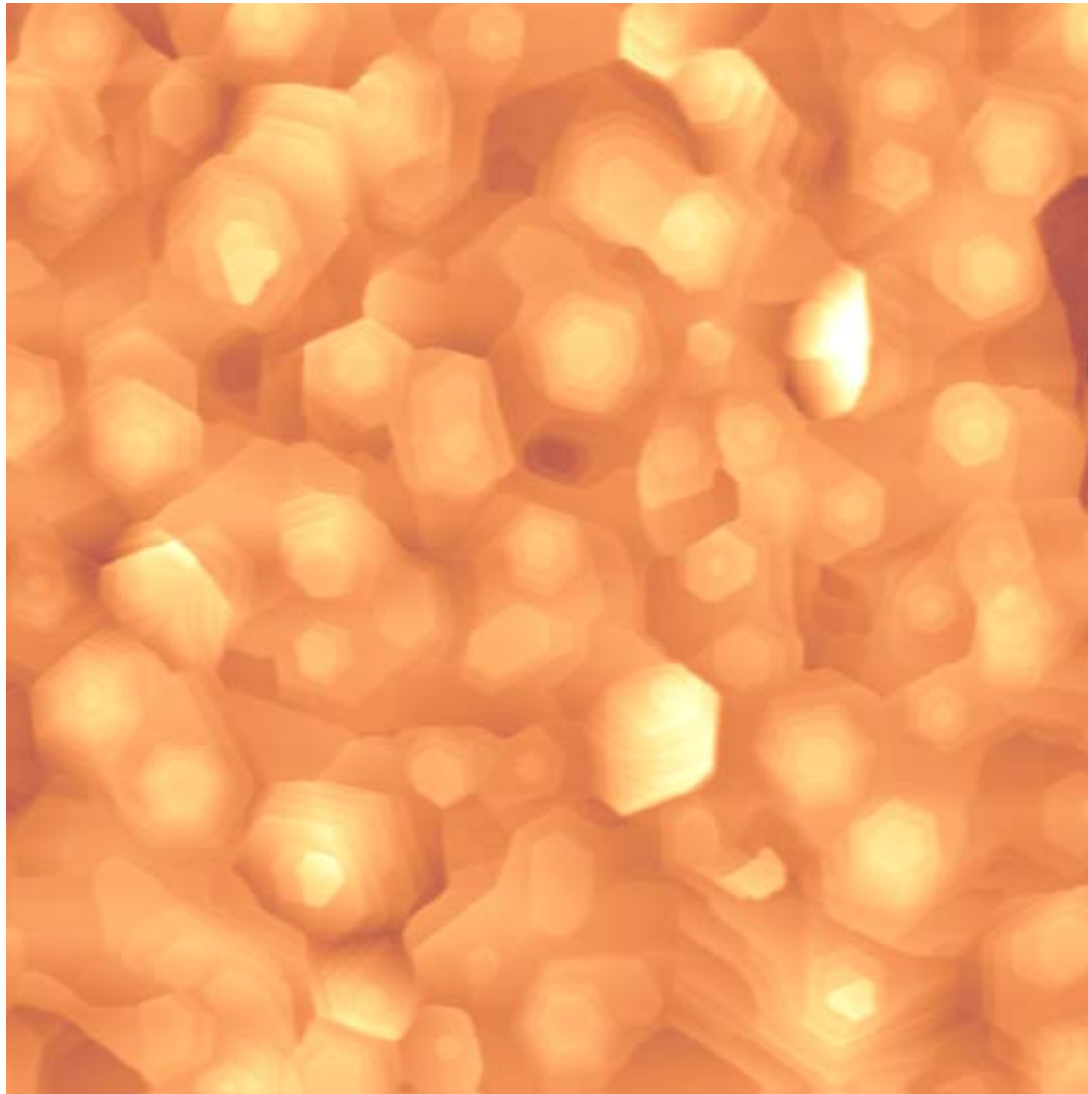
## Or alternatively - A search of Majorana fermions ....

- **Large junctions** Au -  $\text{Bi}_2\text{Se}_3$  - **nox**/NbN  
with overlap area of  $100 \times 30 = 3000 \mu\text{m}^2$   
Native oxide (nox) barrier:  $\sim 1-2 \text{ nm}$   $\text{Nb}_2\text{O}_5/\text{Nb}_2\text{NO}_4/\text{NbN}_{0.5}\text{O}_{0.5}$
- **Ramp junctions** Smaller, with  $\sim 5 \times 0.5 \mu\text{m}^2$  junction area, and a **nox** barrier
- **Bilayers** of 10 nm  $\text{Bi}_2\text{Se}_3$ /70 nm NbN  
even smaller area of **a few nm diameter**  
prepared in-situ, without a native oxide (nox) layer.  
Barrier is between the crashed STM tip and the  $\text{Bi}_2\text{Se}_3$  layer.

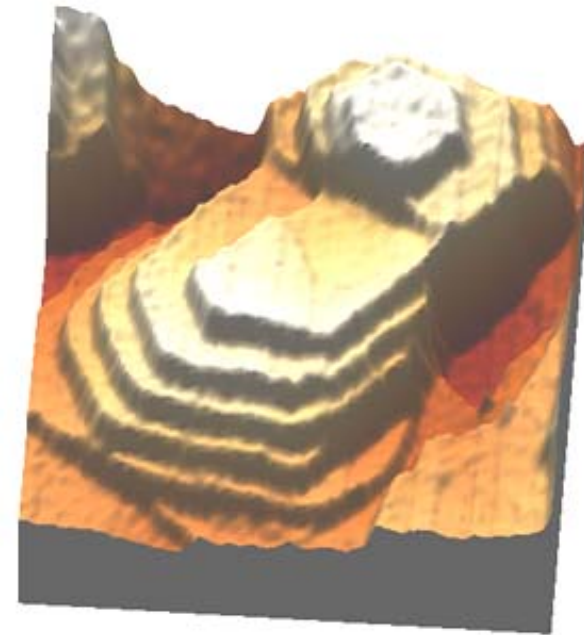
Gad Koren  
Faculty of Physics, Technion

In collaboration with Tal Kirzhner, Yoav Kalcheim & Oded Millo

AFM images of the 400nm thick  $\text{Bi}_2\text{Se}_3$  film on (111)  $\text{SrTiO}_3$



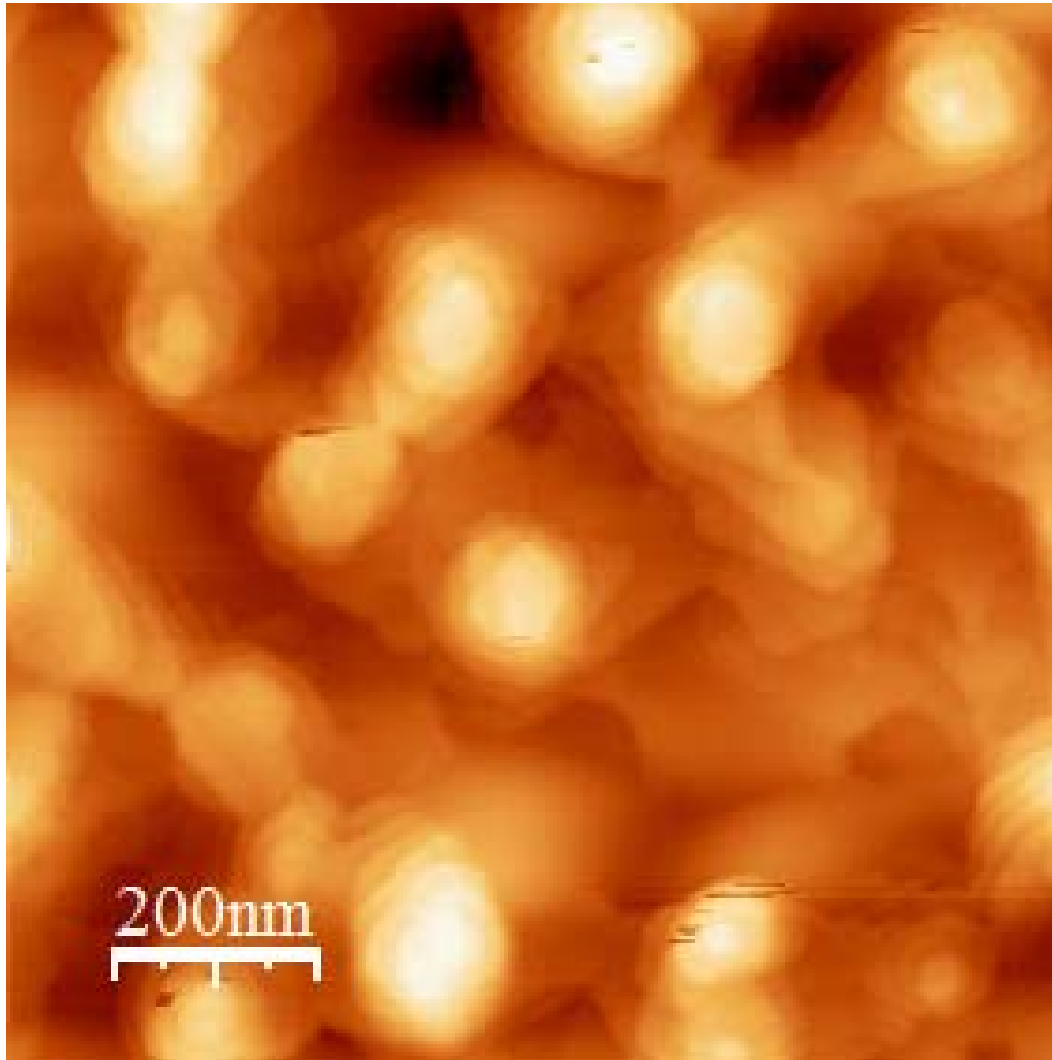
$2 \times 2 \mu\text{m}^2$



$0.3 \times 0.3 \mu\text{m}^2$

Hexagonal & epitaxial  
c-axis:  $d=2.84 \text{ nm}$   
 $(0,0,3n)$  peaks in x-ray

An AFM image of a  
100nm thick  $\text{Bi}_2\text{Se}_3$  on 70nm thick NbN bilayer on (100)  $\text{SrTiO}_3$

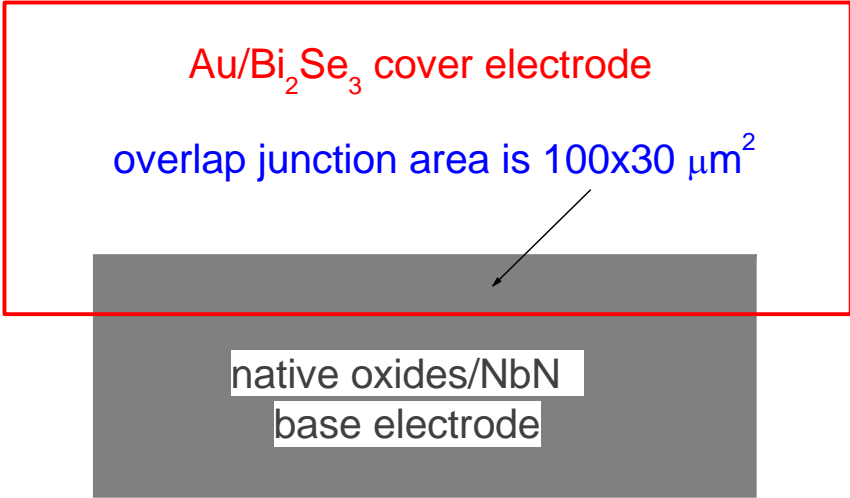


$1 \times 1 \mu\text{m}^2$

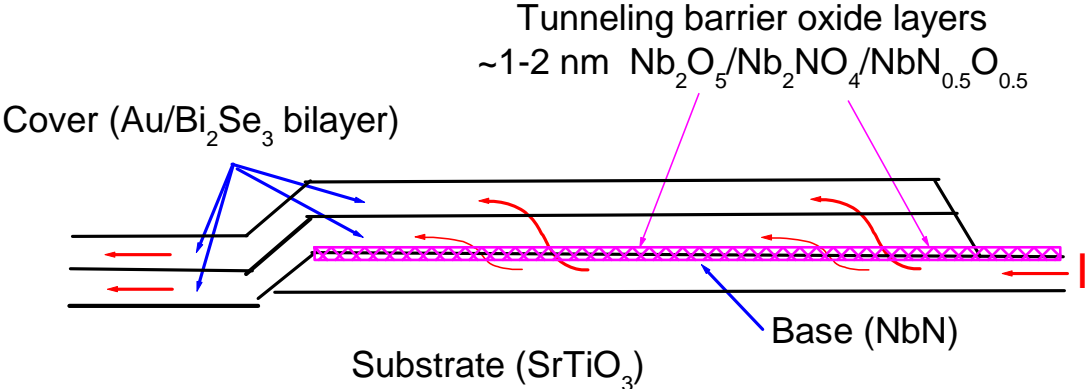
Crystallized well,  
in laterally disordered  
hexagonal form  
Mosaic structure

# Schematic drawings of a large junction layout

Top view of a shadow masked junction



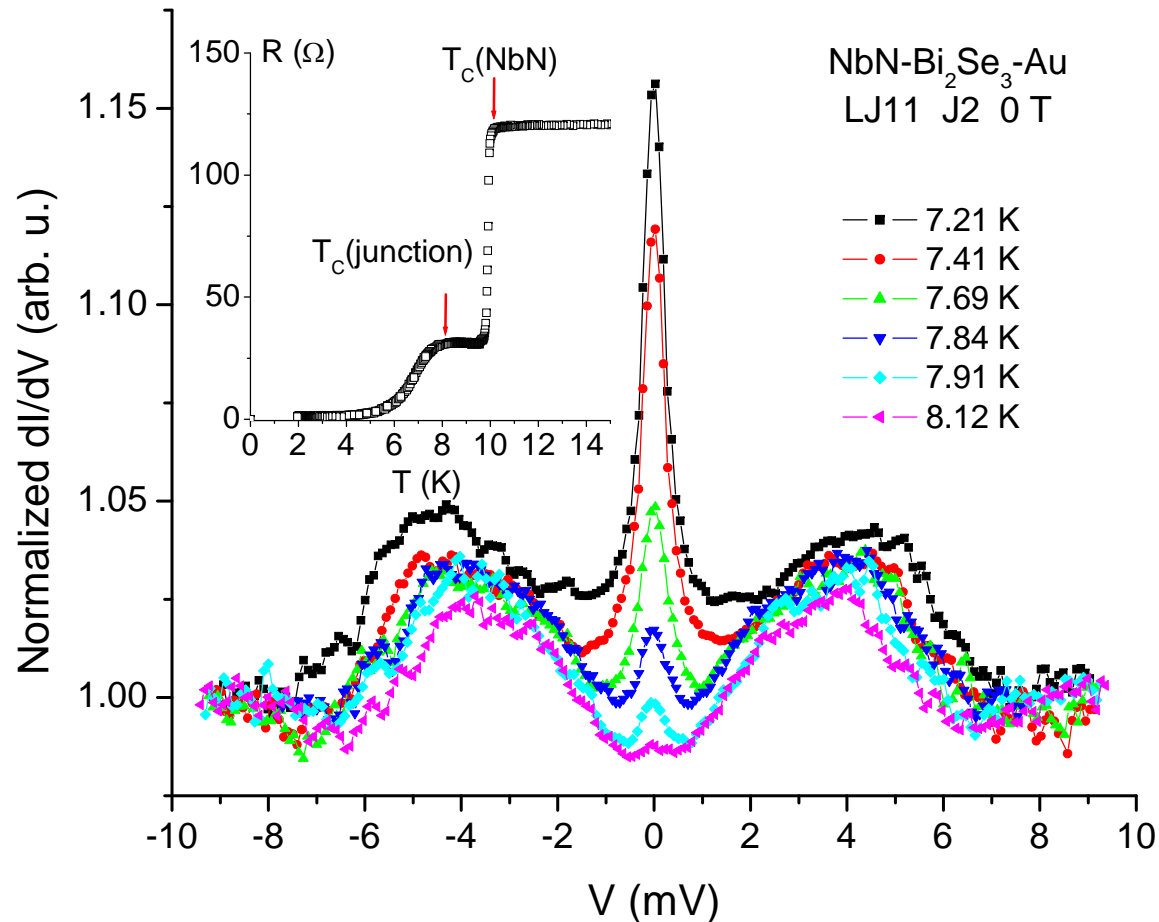
Junction cross-section



“nox” is the native oxide



R at various T and conductance spectra of a large junction near  $T_c$   
 70nm NbN-1 to 2nm oxides-20nm  $\text{Bi}_2\text{Se}_3$ -100nm Au



- R vs T shows a **proximity effect** in  $\text{Bi}_2\text{Se}_3$  below  $T_c \sim 8$  K of the junction
- ZBCP vanishes above  $T_c$  (junction),
- Coherence peaks survive up to  $T_c$  of the NbN electrode
- <http://lanl.arxiv.org/abs/1303.0652>

Previous results: Koren & Kirzhner, PRB **86**, 144508 (2012)  
 NbN – Bi<sub>2</sub>Se<sub>3</sub> - Au

Comparison of fits with different pair potentials

- Singlet s-wave
- Triplet p-wave with Eu(2) pair potential:

$$\Delta_{\uparrow\uparrow} = \Delta_0 \sin \theta (\cos \phi + i \sin \phi)$$

or Eu(1) pair potential:

$$\Delta_{\uparrow\uparrow} = \Delta_0 \sin \theta (\cos \phi + \sin \phi)$$

- Singlet d-wave  $d_{x^2-y^2}$

$$\Delta_{\uparrow\downarrow} = \Delta_0 (\cos 2\phi - \cos 2\alpha)$$

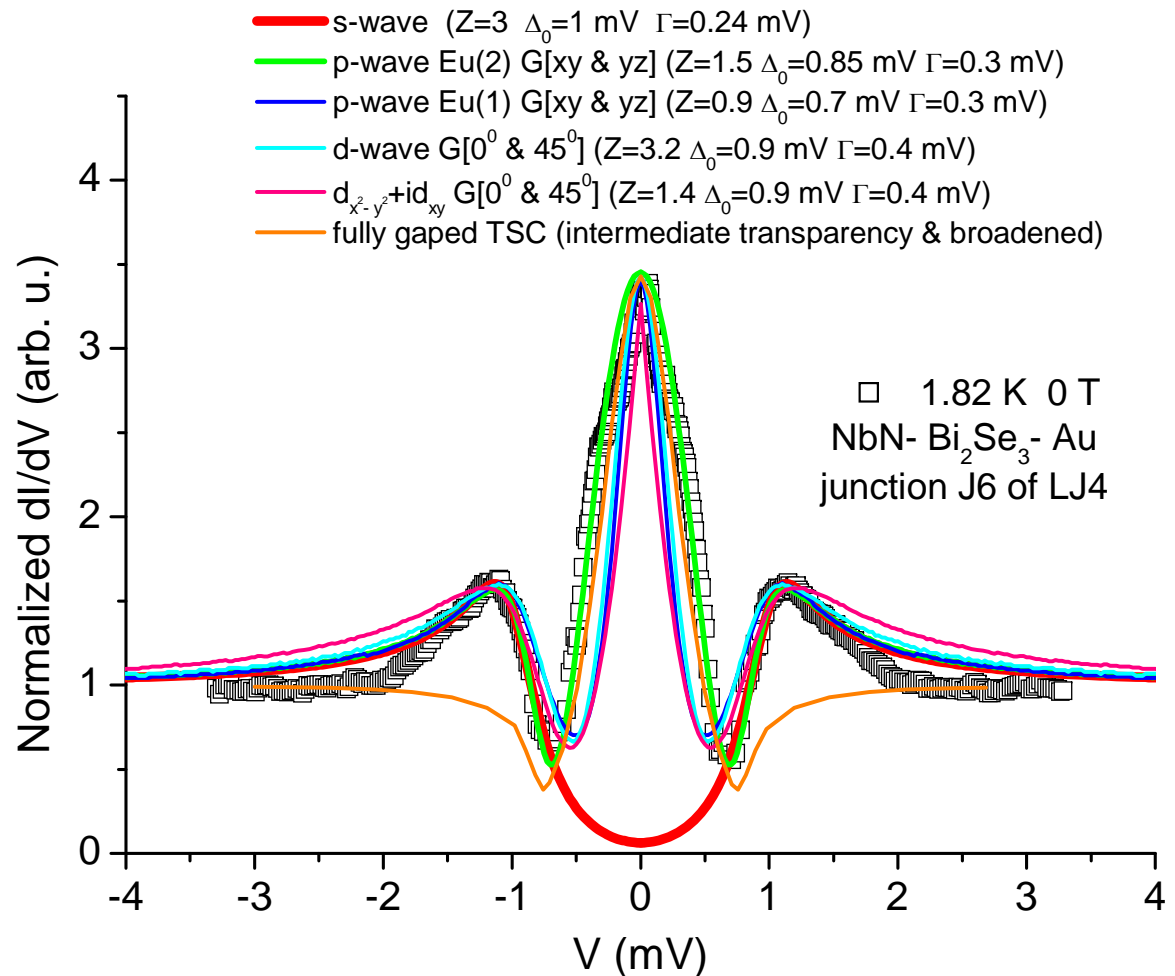
Where  $\alpha$  is either  $0^\circ$  or  $45^\circ$

- Or  $d_{x^2-y^2} + id_{xy}$  at  $0^\circ$  or  $45^\circ$

- Topological SC (TSC)

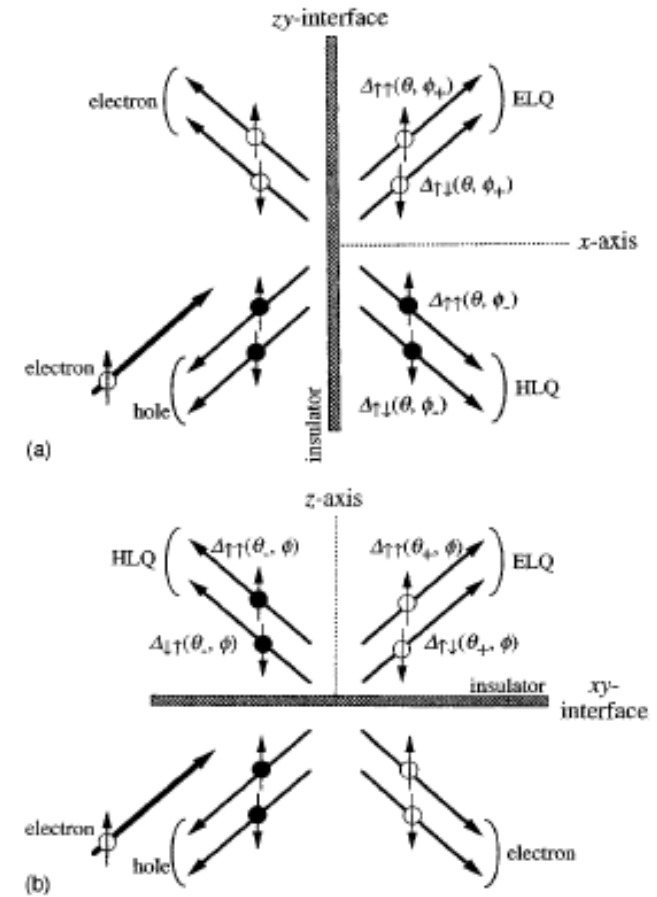
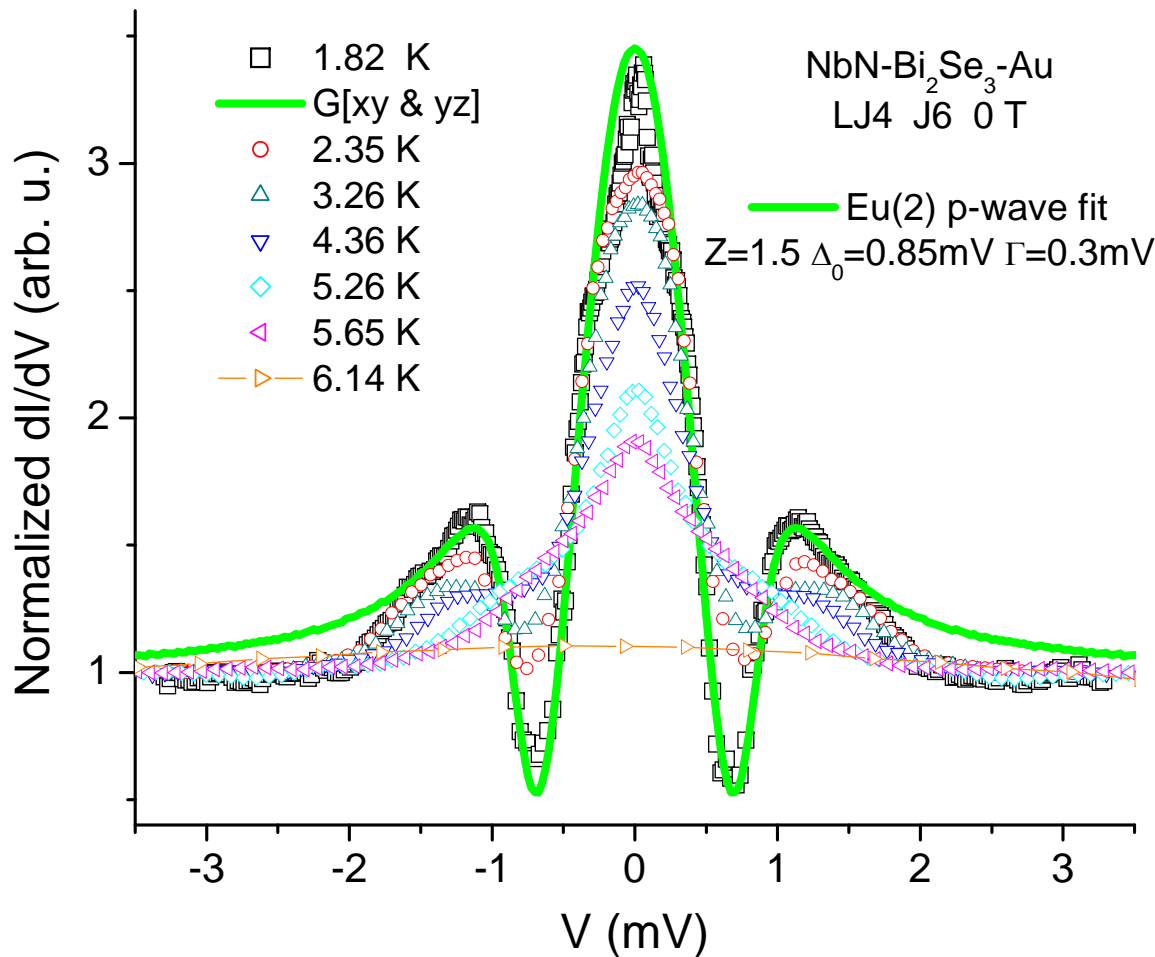
Yamakage... & Tanaka

PRB **85**, 180509(R) (2012)



We ignored the hexagonal symmetry in the fits, but took weighted sums of  $G(xy)$  &  $G(xz)$  or  $G(0^\circ)$  &  $G(45^\circ)$ , that should be averaged over it (hexagonal yielded similar results)

PRB **86**, 144508 (2012): same NbN-Bi<sub>2</sub>Se<sub>3</sub>-Au junction at various T

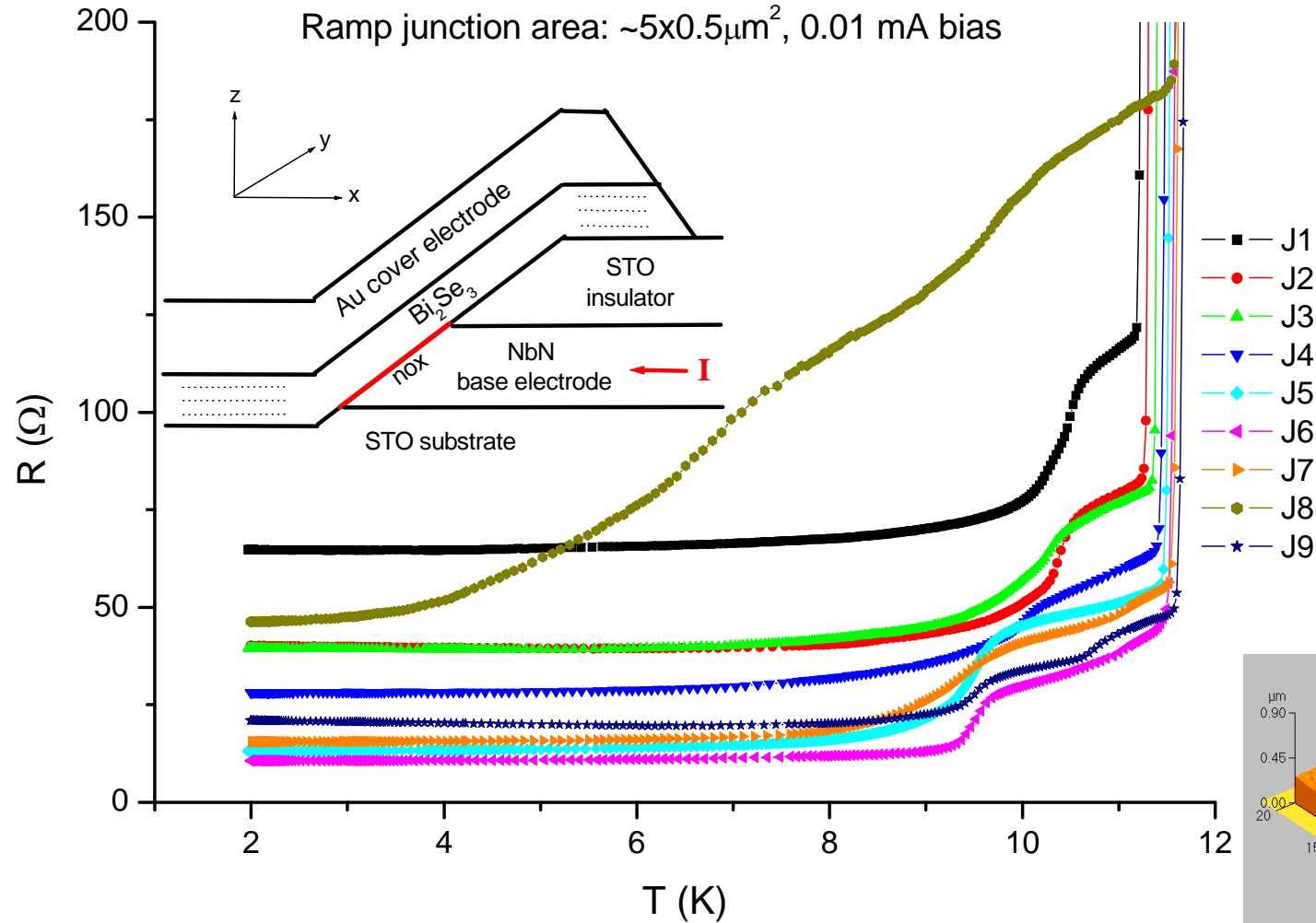


Yamashiro, PRB **56**, 7847 (1997)

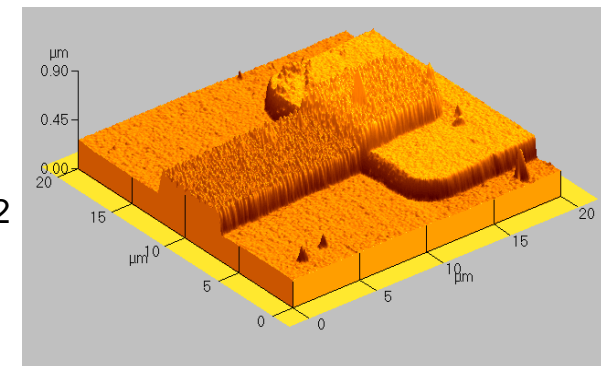
- ZBCP is suppressed with increasing T
- P-wave fit with Eu(2) pair potential:  $\Delta = \Delta_0 \sin \theta (\cos \phi + i \sin \phi)$   
using the same  $Z$ ,  $\Delta_0$  &  $\Gamma$  parameters for the two interfaces

# Ramp junction geometry & R vs T of all RJ on the wafer

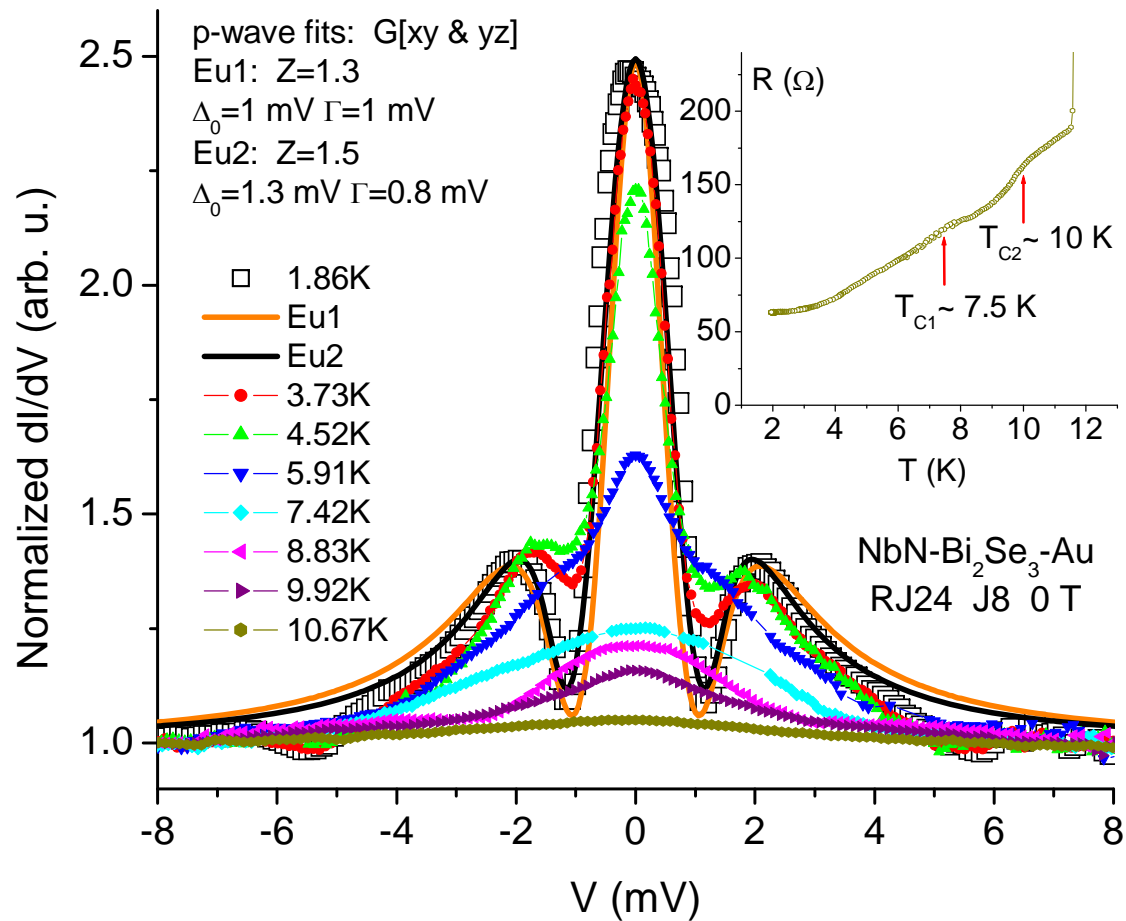
RJ24: NbN-Bi<sub>2</sub>Se<sub>3</sub>-Au junctions  
80nm Au/70nm Bi<sub>2</sub>Se<sub>3</sub> on 60nm STO/70nm NbN  
Ramp junction area:  $\sim 5 \times 0.5 \mu\text{m}^2$ , 0.01 mA bias



- Proximity transition at 10-11 K
- Second transition, see next

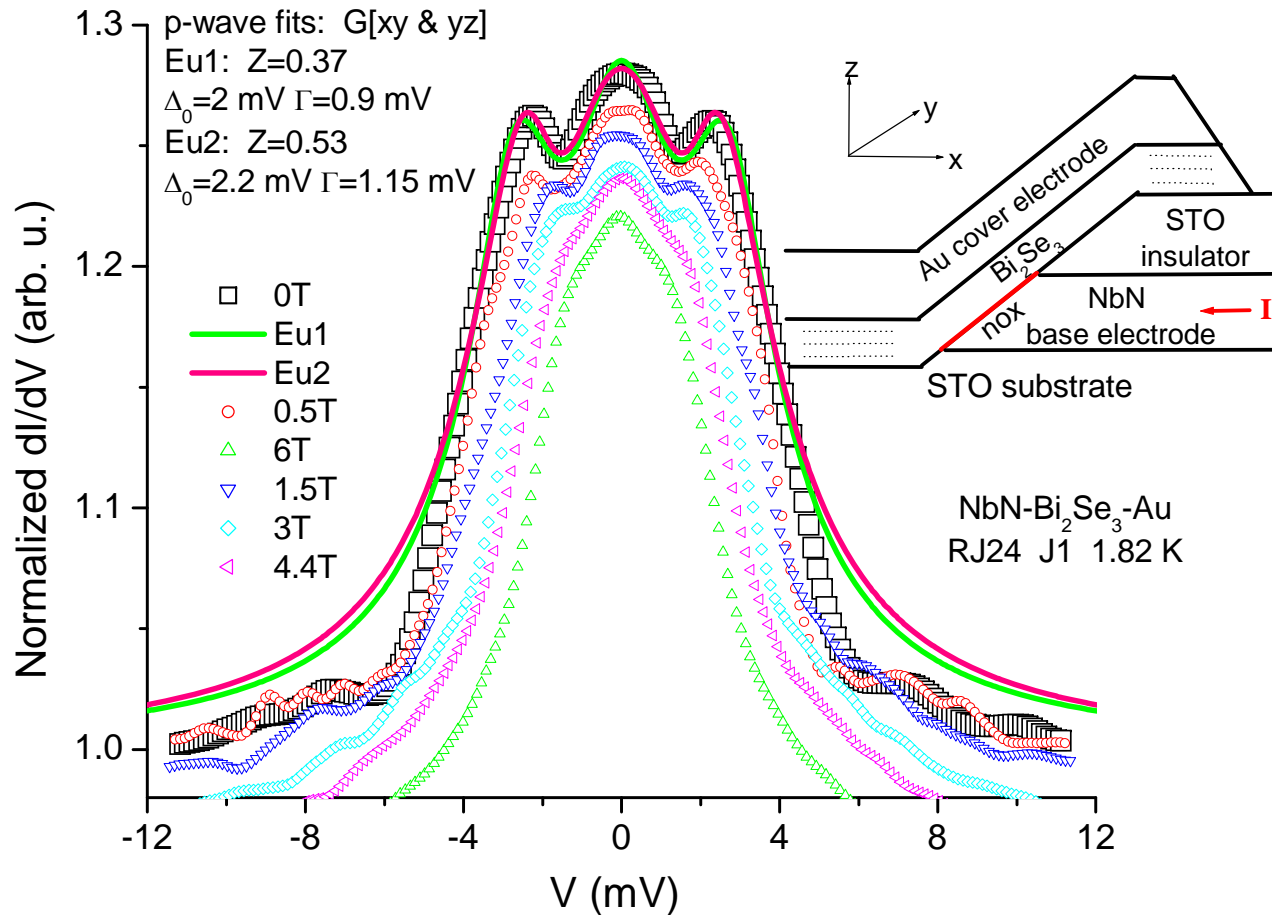


# Ramp junction at various T: NbN-Bi<sub>2</sub>Se<sub>3</sub>-Au



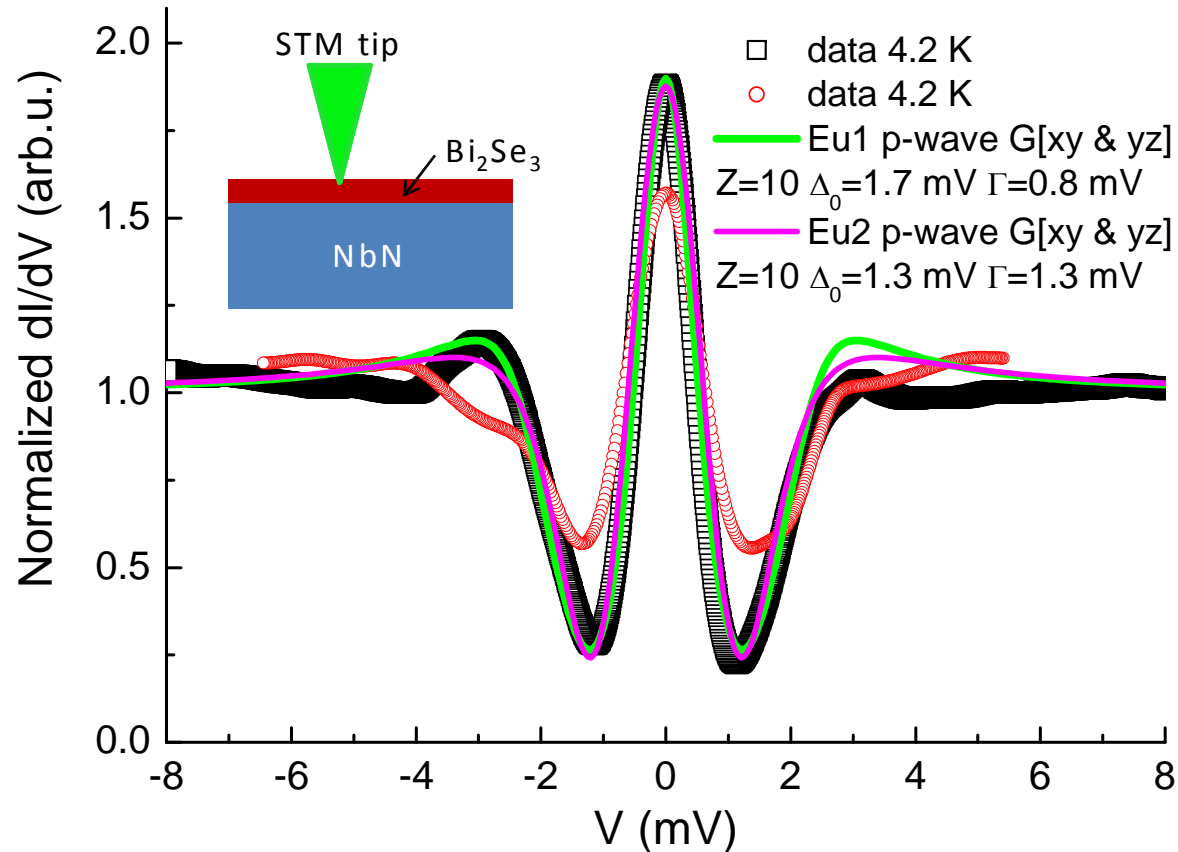
- ZBCP is suppressed with increasing T
- Above 7.5 K only the broad peak survives
- P-wave fits with Eu(2) pair potential:  $\Delta = \Delta_0 \sin \theta (\cos \phi + i \sin \phi)$   
 & Eu(1) pair potential:  $\Delta = \Delta_0 \sin \theta (\cos \phi + \sin \phi)$

# Ramp junction at various H: NbN-Bi<sub>2</sub>Se<sub>3</sub>-Au




- A more transparent junction, **Andreev-like spectra** with small CP & ZBCP
- P-wave fits with Eu(2) pair potential:  $\Delta = \Delta_0 \sin \theta (\cos \phi + i \sin \phi)$   
 & Eu(1) pair potential:  $\Delta = \Delta_0 \sin \theta (\cos \phi + \sin \phi)$

# Crashed STM tip on a bilayer (Point-Contact spectra) at 4.2 K



- No clear SC was measured on the **bare** (oxidized) NbN surface, or on the (deteriorated) bilayer surface before the tip crashing
- Tunneling spectra after crashing the tip into the surface of the **bilayer** are shown in the figure. **These are point contact spectra, measured on a few nm contact area.**
- P-wave fits with Eu(2) pair potential:  $\Delta = \Delta_0 \sin \theta (\cos \phi + i \sin \phi)$   
 & Eu(1) pair potential:  $\Delta = \Delta_0 \sin \theta (\cos \phi + \sin \phi)$

# Conclusions

- ZBCPs and coherence peaks were observed in the in conductance spectra of **many types** of junctions
- Triplet p-wave pair potential fitted all the spectra best when using the modified BTK theory with a minimal number of parameters
- A TSC model failed to fit our data (no CPs)
- Therefore, we apparently do not observe MFs   
but seem to observe an equal-spins (spin-full) triplet SC 